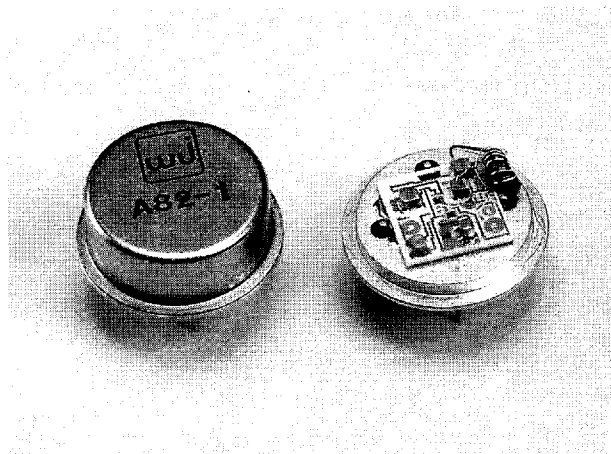


WJ-A82-1 / SMA82-1

20 to 250 MHz
TO-8 CASCADABLE AMPLIFIER

- ◆ AVAILABLE IN SURFACE MOUNT
- ◆ HIGH REVERSE ISOLATION: > 34 dB (TYP.)
- ◆ HIGH OUTPUT POWER: +15.5 dBm (TYP.)
- ◆ HIGH GAIN: 18 dB (TYP)
- ◆ LOW OUTPUT VSWR : 1.1:1 (TYP.)



Specifications*

Characteristics	Typical	Guaranteed	
		0° - 50°C	-54°C - +85°C
Frequency (Min.)	20-300 MHz	20-250 MHz	20-250 MHz
Small Signal Gain (Min.)	18 dB	16.5 dB	16.0 dB
Gain Flatness (Max.)	+0.5 dB	+0.7 dB	+1.0 dB
Noise Figure (Max.)	4.0 dB	4.5 dB	5.0 dB
Power Output at 1 dB Compression (Min.)	+15.5 dBm	+14.0 dBm	+13.5 dBm
VSWR (Max.)			
Input	1.6:1	1.9:1	2.0:1
Output	1.1:1	1.3:1	1.3:1
DC Current (Max.) at +15 Volts	50 mA	52 mA	54 mA

*Measured in a 50-ohm system at +15 Vdc Nominal.

Notes:

1. WJ-CA82-1 is a standard WJ-A82-1 installed in a miniature SMA connector housing and guaranteed over 0°C to 50°C temperature range.

Typical Intermodulation Performance at 25°C

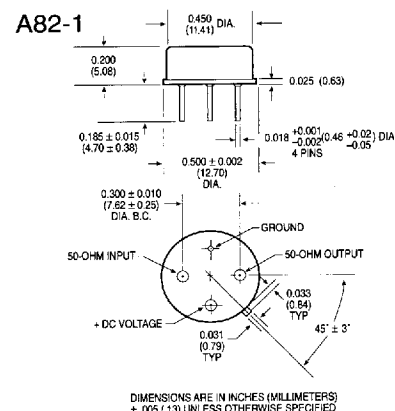
Second Order Harmonic Intercept Point.....38 dBm (Typ.)
Second Order Two Tone Intercept Point30 dBm (Typ.)
Third Order Two Tone Intercept Point.....28 dBm (Typ.)

Absolute Maximum Ratings

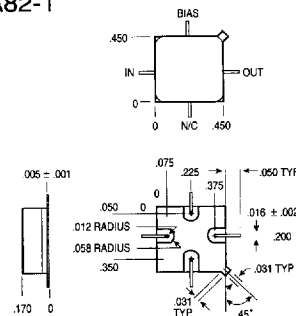
Storage Temperature-62°C to 125°C
Maximum Case Temperature125°C
Maximum DC Voltage.....+17 Volts
Maximum Continuous RF Input Power+10 dBm
Maximum Short Term RF Input Power (1 Minute Max.).....50 Milliwatts
Maximum Peak Power0.5 Watt (3 μsec Max.)
“S” Series Burn-in Temperature (Case).....125°C

Weight approximately 2.0 grams (0.07oz.)

Outline Drawings

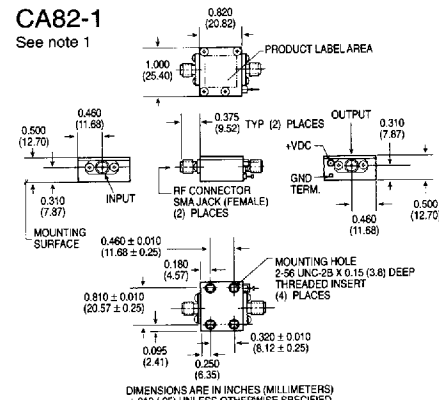


SMA82-1



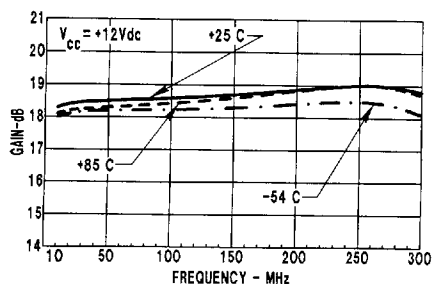
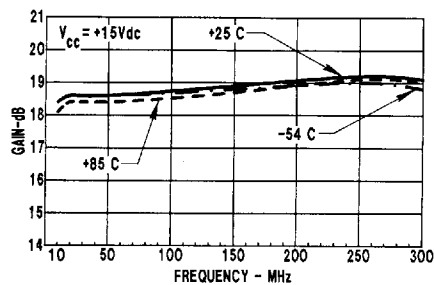
CA82-1

See note 1

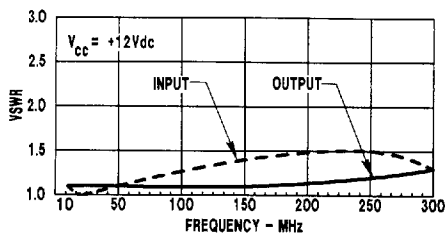
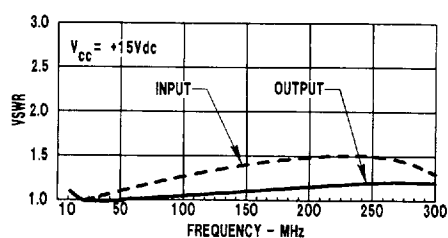


Typical Performance at 25°C

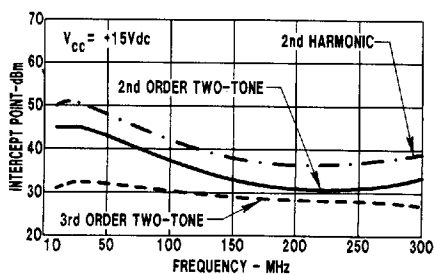
Gain vs. Temperature



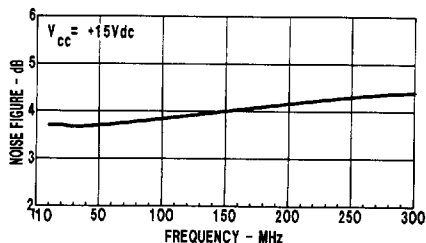
Input/Output VSWR



Intercept Points



Noise Figure



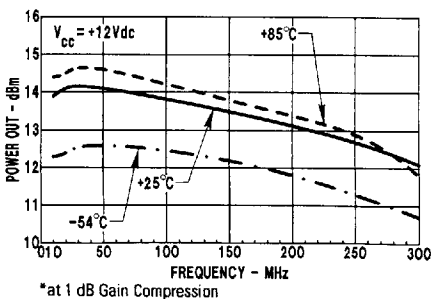
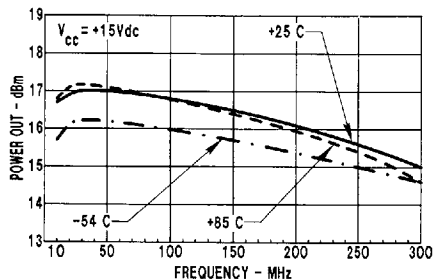
V_{cc} = 15.0 V

Frequency MHz	VSWR IN	VSWR OUT	GAIN DB
2.0	2.1	1.3	18.2
5.0	1.3	1.1	19.5
10.0	1.2	1.1	19.6
20.0	1.1	1.1	19.7
50.0	1.1	1.1	19.8
100.0	1.1	1.1	19.8
150.0	1.2	1.1	20.0
200.0	1.3	1.1	20.0
250.0	1.4	1.1	19.7
300.0	1.5	1.2	19.1
350.0	1.6	1.3	18.0
400.0	1.6	1.5	16.7

Linear S-Parameters

Frequency MHz	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2.0	.360	-65	8.133	-136	.014	41	.139	142
5.0	.141	-94	9.458	-164	.018	16	.066	93
10.0	.072	-113	9.561	-174	.019	8	.042	66
20.0	.042	-142	9.632	-179	.019	2	.035	41
50.0	.035	-129	9.754	-166	.019	-5	.034	16
100.0	.065	65	9.822	-149	.018	-13	.037	-3
150.0	.096	19	9.943	-131	.017	-21	.038	-33
200.0	.131	-17	9.994	-112	.015	-26	.040	-80
250.0	.164	-55	9.684	-92	.014	-26	.059	-135
300.0	.196	-90	9.037	-70	.012	-24	.097	-177
350.0	.228	-123	7.944	-49	.012	-16	.147	-153
400.0	.244	-151	6.804	-30	.013	-10	.192	-128

Output Power vs. Temperature *



*at 1 dB Gain Compression

Thermal Data: V_{cc} = 15 Vdc

Thermal Resistance θ_{jc} 45°C/W
 Transistor Power Dissipation P_d 0.167 W
 Junction Temperature Rise Above Case T_{jc} ... 8°C